



MPW6 K WD

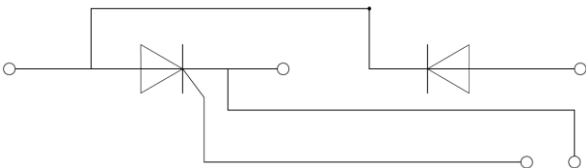
W P g

I d

S g f V d

Sd d	Yd	X
°C		

D fd



De Pd Ud

Sd d	F g	V e	Yd	X
	°C			
				°C
				°C



H f f d F d df f

Sd d	F g	V e	Yd			X
			P 1	W 1	Pd 1	
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					

R g L d

G f	P d	S d f d		L E	S F d

W f d H f f d) W d F d d f f

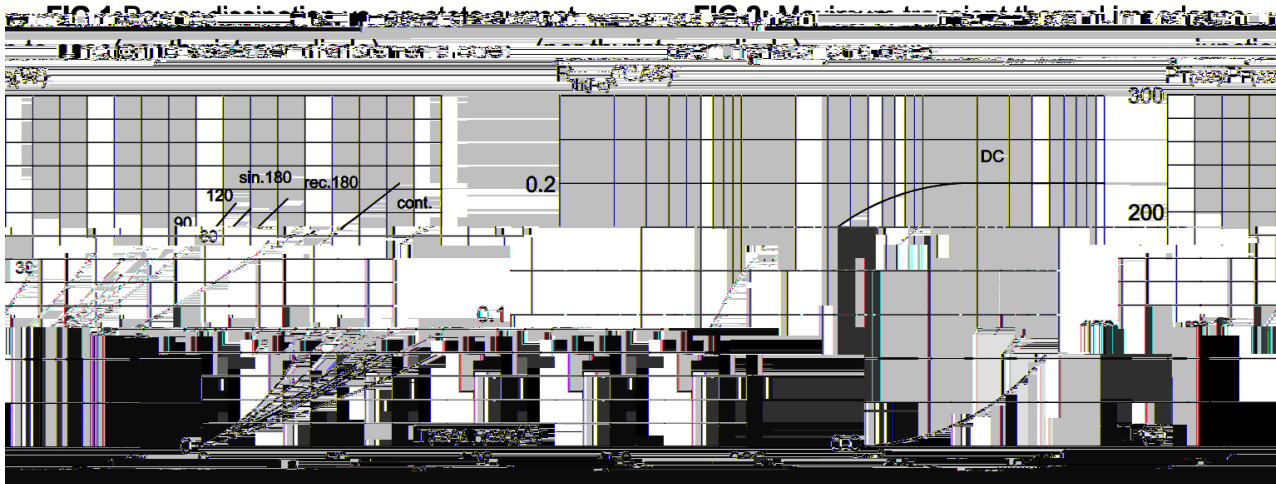


FIG.3:Forward characteristics
(per thyristor or diode)

FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature
 $I_{GT, IH, IL}(T_J)/I_{GT, IH, IL}(T_J=25^\circ\text{C})$

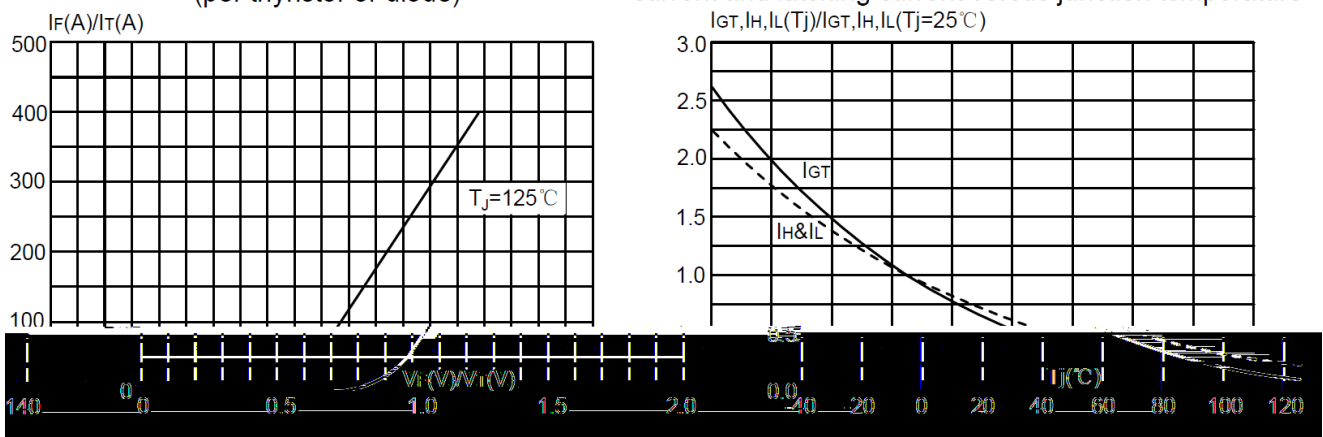


FIG.5: Gate trigger characteristics

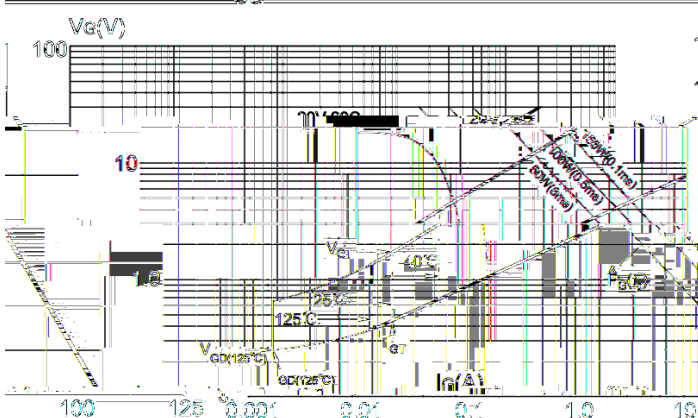
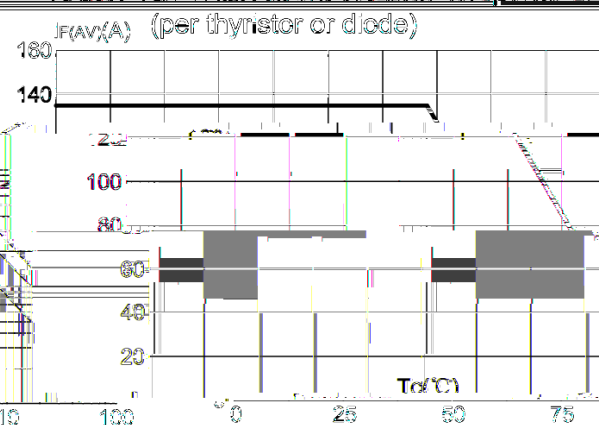
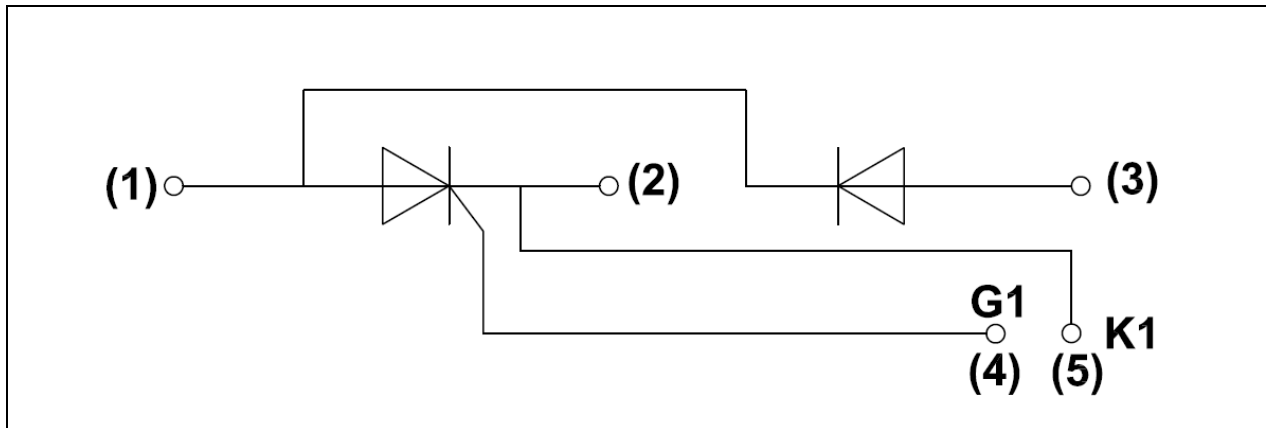
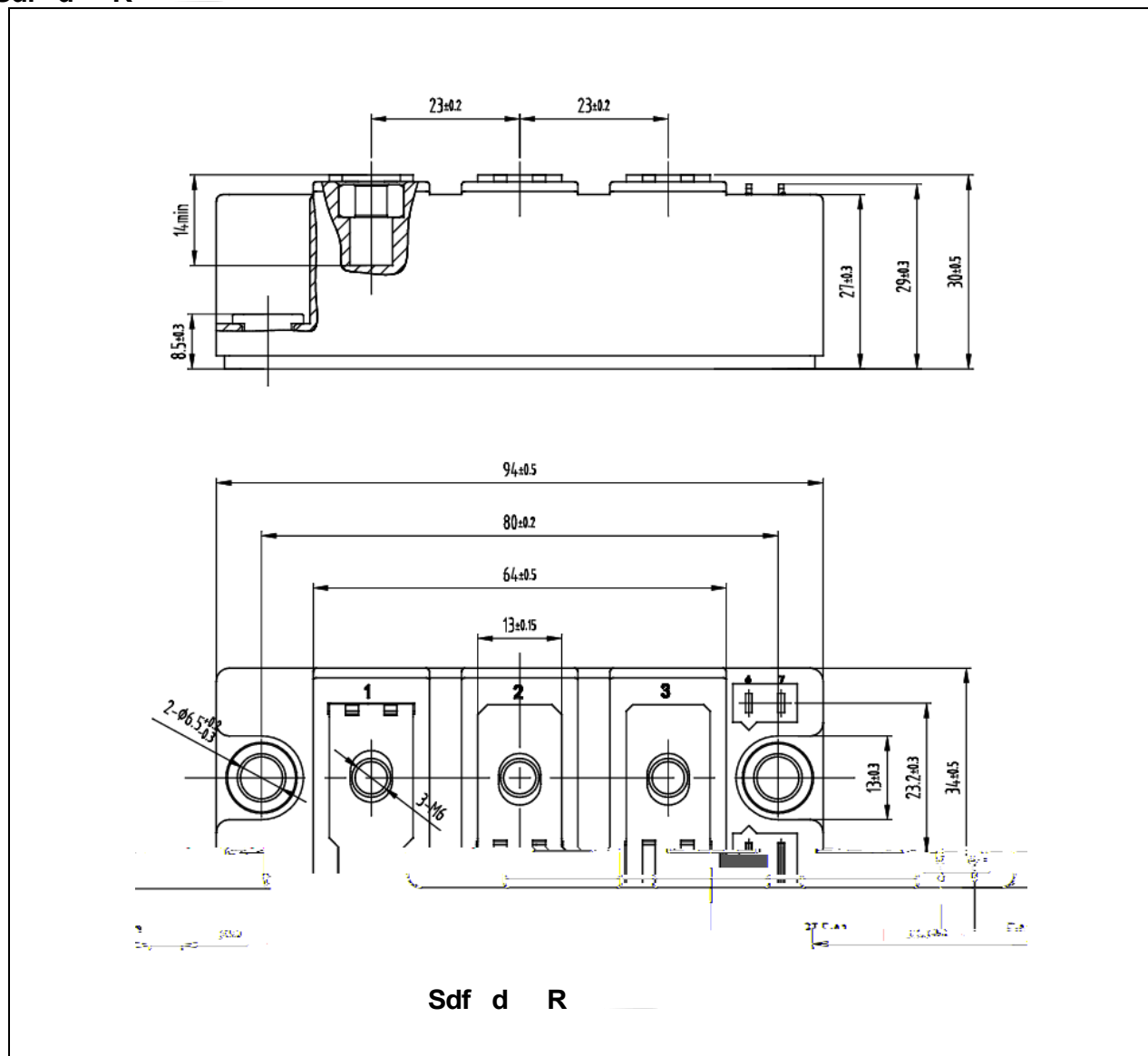


FIG.6: Forward current vs. case temperature



F f G d d

Sdf d R




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